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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10001314	FILING DATE 11/14/2001	CLASS 438	SUBCLASS -1.2	GAU 2812	EXAMINER
**APPLICANTS: Kim Chang; Kim Wan;					
**CONTINUING DATA VERIFIED:					
BEST AVAILABLE COPY					
** FOREIGN APPLICATIONS VERIFIED: REPUBLIC OF KOREA 2001-15415 03/24/2001					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO	
Verified and Acknowledged Examiners's initials				TJK/ 204	
TITLE : Method for forming isolation layer of semiconductor device					

U.S. DEPT. OF COMM./PAT & TM-PTO-436 (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Applicati n Examiner	
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